

Module 2 Unit 1

SEMICONDUCTORS - FORMULAS

(As per Revised Curriculum SVU R-2023)

1. Number of atoms per unit volume	$N = \frac{D \times N_0}{M}$
2. Intrinsic carrier concentration	$n = p = n_i = \sqrt{N_C N_V} \exp\left(-\frac{E_g}{2kT}\right)$
3. Extrinsic carrier concentration	<p><u>N-type:</u></p> <ul style="list-style-type: none"> Majority carriers: $n_n \approx N_D$ at RT Minority carriers: $p_n \approx \frac{n_i^2}{N_D}$ at RT $n = N_C \exp\left(-\frac{E_C - E_F}{kT}\right)$ at moderate temperatures <p><u>P-type:</u></p> <ul style="list-style-type: none"> Majority carriers: $p_p \approx N_A$ at RT Minority carriers: $n_p \approx \frac{n_i^2}{N_A}$ at RT $p = N_V \exp\left(-\frac{E_F - E_V}{kT}\right)$ at moderate temperatures
4. Conductivity and resistivity	<p><u>Conductivity:</u></p> <p>Intrinsic: $\sigma_i = qn_i(\mu_n + \mu_p)$</p> <p>N-type: $\sigma_n = qn\mu_n$</p> <p>P-type: $\sigma_p = qp\mu_p$</p> <p><u>Resistivity:</u> $\rho = \frac{1}{\sigma}$</p>
5. Drift velocity and mobility	<p><u>Drift velocity:</u></p> <p>$v_d = \mu \varepsilon$</p> <p><u>Mobility:</u></p> <p>$\mu = \frac{q\langle\tau\rangle}{m^*}$; $\langle\tau\rangle$: average charge carrier lifetime</p>
6. Drift current density	<p><u>Electrons:</u></p> <p>$J_n(\text{drift}) = qn\mu_n \varepsilon = \sigma_n \varepsilon$</p> <p><u>Holes:</u></p> <p>$J_p(\text{drift}) = qp\mu_p \varepsilon = \sigma_p \varepsilon$</p>
7. Diffusion current density	<p><u>Electrons:</u></p> <p>$J_n(\text{diffusion}) = qD_n \frac{dn}{dx}$</p>

	<p><u>Holes:</u></p> $J_p(\text{diffusion}) = -qD_p \frac{dp}{dx}$
8. Einstein's relation	$\frac{D}{\mu} = \frac{kT}{q} = \text{constant at a given temperature}$
9. Probability factor for occupation of energy level E (Fermi-Dirac function)	<p><u>Electrons:</u></p> $F(E) = \frac{1}{1 + \exp\left(\frac{E - E_F}{kT}\right)}$ <p><u>Holes:</u></p> $1 - F(E) = \frac{\exp\left(\frac{E - E_F}{kT}\right)}{1 + \exp\left(\frac{E - E_F}{kT}\right)}$
10. Position of Fermi level in intrinsic semiconductors	$E_F = E_i = \frac{E_C + E_V}{2} + \frac{3}{4} kT \ln \frac{m_h^*}{m_e^*}$ $\approx \frac{E_C + E_V}{2} = \frac{E_g}{2}$
11. Fermi level shift due to doping	<p><u>N-type:</u></p> $E_F - E_i = kT \ln \left(\frac{n}{n_i}\right); n \approx N_D \text{ at RT}$ <p><u>P-type:</u></p> $E_F - E_i = -kT \ln \left(\frac{p}{n_i}\right); p \approx N_A \text{ at RT}$ <p>Alternatively, $E_i - E_F = kT \ln \left(\frac{p}{n_i}\right)$</p>